

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L14	11749	(semiconductor layer compound (silicon SAME oxygen SAME nitrogen))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:13
L15	4	(semiconductor layer compound (silicon SAME oxygen SAME nitrogen) material\$1free)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:13
L16	1204	(semiconductor layer compound (silicon NEAR oxygen NEAR nitrogen))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:15
L17	249	(semiconductor layer (compound SAME (silicon NEAR oxygen NEAR nitrogen)) )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:15
L24	1673	257/506.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:31
L25	0	24 (semiconductor layer (compound SAME (silicon NEAR oxygen NEAR nitrogen)) )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:31
L26	539	257/508.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:32
L27	0	26 (semiconductor layer (compound SAME (silicon NEAR oxygen NEAR nitrogen)) )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:32
L28	469	257/522.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:32

L29	0	28 (semiconductor layer (compound SAME (silicon NEAR oxygen NEAR nitrogen))) )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:32
L30	863	257/E23.002.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:33
L31	0	30 (semiconductor layer (compound SAME (silicon NEAR oxygen NEAR nitrogen))) )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:33
L32	513	257/E21.267.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:33
L33	5	32 (semiconductor layer (compound SAME (silicon NEAR oxygen NEAR nitrogen))) )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:33
L34	3333	438/763.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:34
L35	6	34 (semiconductor layer (compound SAME (silicon NEAR oxygen NEAR nitrogen))) )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:34
L36	587	438/681.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:35
L37	1	36 (semiconductor layer (compound SAME (silicon NEAR oxygen NEAR nitrogen))) )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:35
L38	789	438/584.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:35
L39	1	38 (semiconductor layer (compound SAME (silicon NEAR oxygen NEAR nitrogen))) )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	AND	ON	2010/03/01 09:35
S1	28	((ZVONIMIR) near2 (GABRIC)).INV.	US-PGPUB; USPAT	AND	ON	2009/06/02 10:41
S2	19	((WERNER) near2 (PAMLER)).INV.	US-PGPUB; USPAT	AND	ON	2009/06/02 10:48

S3	16	((GUENTHER) near2 (SCHINDLER)).INV.	US-PGPUB; USPAT	AND	ON	2009/06/02 10:48
S4	30628	INFINEON.AS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 10:51
S5	75	S4 (plasma\$1enhanced near ((chemical adj1 vapor adj1 deposition) OR CVD))	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 10:52
S6	2	("20060084236").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/06/02 10:59
S7	2	("6445072").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/06/02 11:03
S8	2	("6211057").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/06/02 11:07
S10	2	("20050079700").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/06/02 11:12
S11	452	(tetraethyl) (plasma\$1enhanced near ((chemical adj1 vapor adj1 deposition) OR CVD))	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 15:53
S12	16	((tetraethyl adj1 orthosilicate) same nitrogen) (plasma\$1enhanced near ((chemical adj1 vapor adj1 deposition) OR CVD))	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 15:54
S13	1	((tetraethyl adj1 orthosilicate) near nitrogen) (plasma\$1enhanced near ((chemical adj1 vapor adj1 deposition) OR CVD))	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 16:03
S14	89	(helium near carrier) (plasma\$1enhanced near ((chemical adj1 vapor adj1 deposition) OR CVD))	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 16:03
S15	81	S14 @pd<="20080901"	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 16:04
S16	7	S12 rate	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 16:11
S17	2	S12 (nitrogen near4 flow)	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 16:40

S18	3	S12 (nitrogen same flow)	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 16:41
S19	16	S12 (nitrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 16:41
S20	194	((tetraethyl adj1 orthosilicate) same nitrogen) ((chemical adj1 vapor adj1 deposition) OR CVD)	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:02
S21	73	S20 (flow adj1 rate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:03
S22	403	257/522.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:43
S23	1	S22 ((tetraethyl adj1 orthosilicate) same nitrogen) ((chemical adj1 vapor adj1 deposition) OR CVD)	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:43
S24	715	257/E23.002.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:44
S25	1	S24 ((tetraethyl adj1 orthosilicate) same nitrogen) ((chemical adj1 vapor adj1 deposition) OR CVD)	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:44
S26	473	257/E21.267.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:44
S27	2	S26 ((tetraethyl adj1 orthosilicate) same nitrogen) ((chemical adj1 vapor adj1 deposition) OR CVD)	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:44
S28	3238	438/763.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:45
S29	2	S28 ((tetraethyl adj1 orthosilicate) same nitrogen) ((chemical adj1 vapor adj1 deposition) OR CVD)	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:45
S30	1913	438/618.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:45
S31	0	S30 ((tetraethyl adj1 orthosilicate) same nitrogen) ((chemical adj1 vapor adj1 deposition) OR CVD)	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:45

S32	549	438/619.cols.	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:45
S33	0	S32 ((tetraethyl adj1 orthosilicate) same nitrogen) ((chemical adj1 vapor adj1 deposition) OR CVD)	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:46
S34	105	S30 (nitrogen same flow)	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:46
S35	11	S32 (nitrogen same flow)	US-PGPUB; USPAT; EPO; JPO; DERWENT	AND	ON	2009/06/02 17:47
S36	0	SiOHCN layer	US-PGPUB; USPAT	AND	ON	2009/06/03 08:37
S37	0	Si\$2O\$2H\$2O\$1N layer	US-PGPUB; USPAT	AND	ON	2009/06/03 08:38
S38	0	(silicon adj1 oxygen adj1 hydrogen adj1 carbon adj1 nitrogen) layer	US-PGPUB; USPAT	AND	ON	2009/06/03 08:39
S39	0	(silicon adj1 oxygen adj1 hydrogen adj1 carbon adj1 nitrogen)	US-PGPUB; USPAT	AND	ON	2009/06/03 08:39
S40	0	SiOHCN	US-PGPUB; USPAT	AND	ON	2009/06/03 08:39
S41	0	Si\$2O\$2H\$2O\$1N	US-PGPUB; USPAT	AND	ON	2009/06/03 08:39
S42	2	("6445072").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/10/28 11:51
S43	2	("6211057").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/10/28 11:54

## EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	((("semiconductorstructuresubstratelayercompound (siliconnearoxygennearnitrogen)") or ("intermediateadj1layer)(cover \$4adj1layer)subareamaterial\$1freesaeal\$4enviroment).clm.")).PN.	US-PGPUB; USPAT; UPAD	OR	OFF	2010/03/01 09:07

L18	228	(semiconductor layer (compound SAME (silicon NEAR oxygen NEAR nitrogen)) )	US-PGPUB; USPAT; UPAD	AND	ON	2010/03/01 09:16
L19	4	(semiconductor layer compound (silicon SAME oxygen SAME nitrogen) material\$1free)	US-PGPUB; USPAT; UPAD	AND	ON	2010/03/01 09:17
L21	12	(semiconductor layer (compound SAME (silicon NEAR oxygen NEAR nitrogen)) ).clm.	US-PGPUB; USPAT; UPAD	AND	ON	2010/03/01 09:18
L22	12	21 "257".clas.	US-PGPUB; USPAT; UPAD	AND	ON	2010/03/01 09:30
L23	8	21 "438".clas.	US-PGPUB; USPAT; UPAD	AND	ON	2010/03/01 09:30
S44	1	"Term Removed"	US-PGPUB; USPAT; UPAD	OR	OFF	2009/10/28 14:10
S45	1	"Term Removed"	US-PGPUB; USPAT; UPAD	OR	OFF	2009/10/29 10:50

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